

ABSTRACT OF THE DISCLOSURE

A photoelectric conversion element is disposed in each of a plurality of recesses of a support. Light reflected by the inside surface of the recess shines on the photoelectric conversion element. The photoelectric conversion element has an approximately spherical shape and has the following structure. The outer surface of a center-siden-type amorphous silicon (a-Si) layer is covered with a p-type amorphous SiC (a-SiC) layer having a wider optical band gap than a-Si does, whereby a pn junction is formed. A first conductor of the support is connected to the p-type a-SiC layer of the photoelectric conversion element at the bottom or its neighborhood of the recess. A second conductor, which is insulated from the first conductor by an insulator, of the support is connected to the n-type a-Si layer of the photoelectric conversion element.